Silicon Schottky Barrier Diode for Rectifying

HITACHI

ADE-208-163D(Z) Rev 4 Jul. 1997

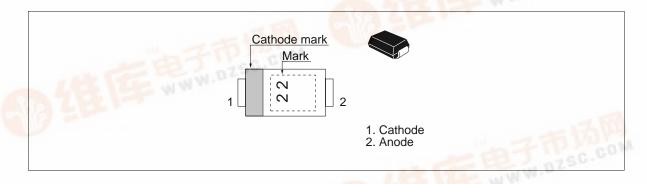
Features

- Good for high-frequency rectify.
- LRP structure ensures higher reliability.

Ordering Information

Type No.	Laser Mark	Package Code
HRF22	22	LRP

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V _{RRM} *1	40	V
Average rectified current	I _o *1	1.0	A
Non-Repetitive peak forward surge current	I _{FSM} *2	20	Α
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

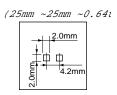
Note: 1. See from Fig.4 to Fig.7

Note: 2. 10msec half sine wave 1 pulse

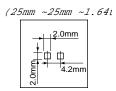
Electrical Characteristics (Ta = 25^{\circ}C)

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V_{F}	_		0.55	V	I _F = 1.0A
Reverse current	I_R	_	_	1.0	mA	$V_R = 40V$
ESD-Capability	_	150	_	_	V	C=200pF , R=0 Ω , Both forward and reverse direction 1 pulse.
Thermal resistance	Rth(j-a)	_	_	108	°C/W	Alumina board *1
		_	_	157		Print board *2

Note: 1. Alumina board



Note: 2. Print board



Main Characteristic

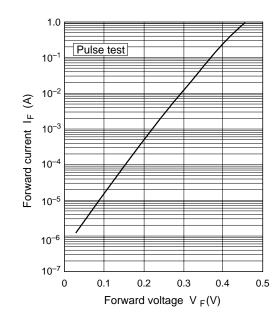
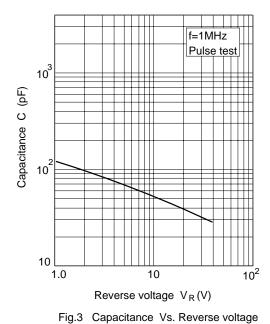


Fig.1 Forward current Vs. Forward voltage



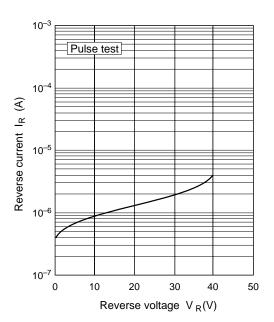


Fig.2 Reverse current Vs. Reverse voltage

Main Characteristic

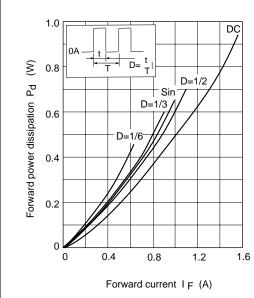


Fig.4 Forward p ower dissipation Vs. Forward current

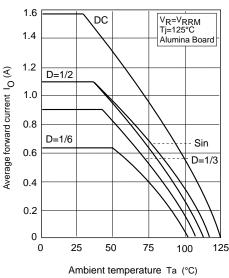


Fig.6 Average forward current Vs. Ambient temperature

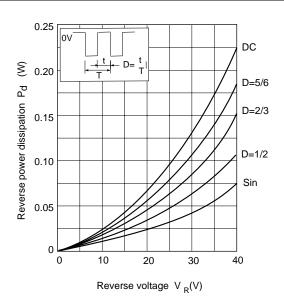


Fig.5 Reverse power dissipation Vs. Reverse voltage

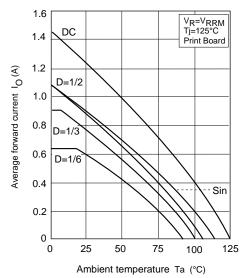
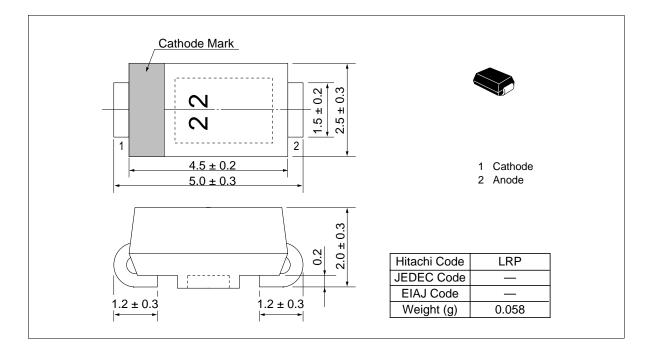


Fig.7 Average forward current Vs. Ambient temperature

Package Dimensions

Unit: mm



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